1) For a 2 dimensional electron gas in GaAs with a density of 1011 cm-2, calculate the Fermi energy and the Fermi wavelength. (This will be important when we discuss quantum dots and quantum point contacts.)

2) Calculate the change in the Gibbs free energy for a two-island circuit with no gates. (I.e. three tunnel junctions in series) for all possible electron transitions. (Left lead to island 1, island 1 to left lead, island 1 to island 2, island 2 to island 1, island 2 to right lead, right lead to island 2). Describe the conditions under which current can and cannot flow from the left lead to the right lead.

3) What is the Fermi wavelength of electrons in aluminum? Is it possible to fabricate 1d Al wires using photolithography? Is it possible to fabricate Al wires using electron beam lithography?

4) Find the resistivity of pure copper at room temperature. Now, find the density of electrons in copper, assuming one free electron per atom. Now, calculate the scattering time and the mean free path of the electrons from the Drude model. Is it possible to fabricate copper wires in the ballistic limit using photolithography? Is it possible to fabricate copper wires in the ballistic limit using electron beam lithography?

5) For a 2DEG in GaAs with  $n=10^{11}$  cm-2 and a mobility of 8,000 cm<sup>2</sup>/V-s (typical of room temperature HEMT operation), calculate the scattering time and the mean free path from the Drude model. Is it possible to fabricate devices using lithography that are smaller than the mean free path? Remember you must use the effective mass of electrons for the Fermi energy, etc.